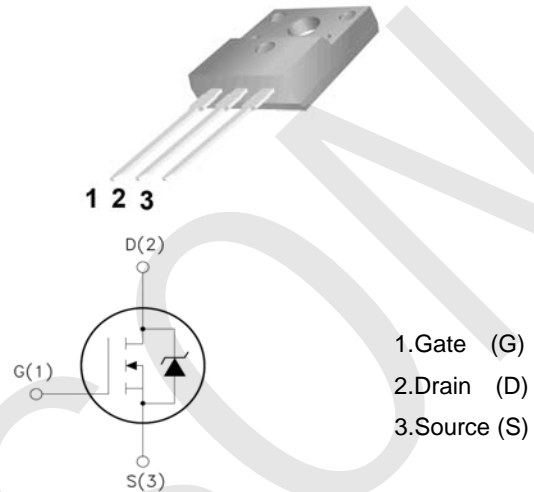


SM2N60S

Features:

- Low Intrinsic Capacitances.
- Excellent Switching Characteristics.
- Extended Safe Operating Area.
- Unrivalled Gate Charge :Qg=6.8nC (Typ.).
- BVDSS=600V,I_D=2A
- R_{DS(on)} : 4.5Ω (Max) @V_G=10V
- 100% Avalanche Tested

TO-220F



Absolute Maximum Ratings (T_a=25°C unless otherwise noted)

| Symbol | Parameter | Value | Unit |
|------------------|--|-----------------------|------|
| V _{DSS} | Drain-Source Voltage | 600 | V |
| I _D | Drain Current | T _c =25°C | 2 |
| | | T _c =100°C | 1.25 |
| V _{GSS} | Gate-Source Voltage | ±30 | V |
| E _{AS} | Single Pulse Avalanche Energy (note1) | 120 | mJ |
| I _{AR} | Avalanche Current (note2) | 2 | A |
| P _D | Power Dissipation (T _c =25°C) | 23 | W |
| T _j | Junction Temperature(Max) | 150 | °C |
| T _{stg} | Storage Temperature | -55~+150 | |
| TL | Maximum lead temperature for soldering purpose, 1/8" from case for 5 seconds | 300 | |

Thermal Characteristics

| Symbol | Parameter | Typ. | Max. | Unit |
|------------------|---|------|------|------|
| R _{θJC} | Thermal Resistance, Junction to Case | - | 5.50 | °C/W |
| R _{θJA} | Thermal Resistance, Junction to Ambient | - | 62.5 | |

Electrical Characteristics (Ta=25°C unless otherwise noted)

| Symbol | Parameter | Test Condition | Min. | Typ. | Max. | Unit |
|---|---|---|------|------|------|------|
| Off Characteristics | | | | | | |
| BV _{DSS} | Drain-Source Breakdown Voltage | I _D =250μA, V _{GS} =0 | 600 | - | - | V |
| ΔBV _{DSS} /ΔT _J | Breakdown Voltage Temperature Coefficient | I _D =250μA, Reference to 25°C | - | 0.6 | - | V/°C |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} =600V, V _{GS} =0V | - | - | 10 | μA |
| | | V _{DS} =480V, T _c =125°C | - | - | 100 | |
| I _{GSSF} | Gate-body leakage Current, Forward | V _{GS} =+30V, V _{DS} =0V | - | - | 100 | nA |
| I _{GSSR} | Gate-body leakage Current, Reverse | V _{GS} =-30V, V _{DS} =0V | - | - | -100 | |
| On Characteristics | | | | | | |
| V _{GS(TH)} | Gate Threshold Voltage | I _D =250μA, V _{DS} =V _{GS} | 2 | - | 4 | V |
| R _{DS(ON)} | Static Drain-Source On-Resistance | I _D =1A, V _{GS} =10V | - | - | 4.5 | Ω |
| Dynamic Characteristics | | | | | | |
| C _{iss} | Input Capacitance | V _{DS} =25V, V _{GS} =0, f=1.0MHz | - | 298 | - | pF |
| C _{oss} | Output Capacitance | | - | 31 | - | |
| C _{rss} | Reverse Transfer Capacitance | | - | 9 | - | |
| Switching Characteristics | | | | | | |
| T _{d(on)} | Turn-On Delay Time | V _{DD} =300V, I _D =2A R _G =25Ω (Note 3,4) | - | 10 | 30 | nS |
| T _r | Turn-On Rise Time | | - | 25 | 60 | |
| T _{d(off)} | Turn-Off Delay Time | | - | 20 | 50 | |
| T _f | Turn-Off Rise Time | | - | 25 | 60 | |
| Q _g | Total Gate Charge | V _{DS} =480V, V _{GS} =10V, I _D =2A (Note 3,4) | - | 6.8 | - | nC |
| Q _{gs} | Gate-Source Charge | | - | 2.0 | - | |
| Q _{gd} | Gate-Drain Charge | | - | 1.8 | - | |
| Drain-Source Diode Characteristics and Maximum Ratings | | | | | | |
| I _S | Max. Diode Forward Current | - | - | - | 2 | A |
| I _{SM} | Max. Pulsed Forward Current | - | - | - | 8 | |
| V _{SD} | Diode Forward Voltage | I _D =2A | - | - | 1.5 | V |
| T _{rr} | Reverse Recovery Time | I _S =2A, V _{GS} =0V diF/dt=100A/μs | - | 380 | - | nS |
| Q _{rr} | Reverse Recovery Charge | (Note3) | - | 0.9 | - | μC |

- Notes : 1, L=60mH, I_{AS}=2A, V_{DD}=50V, R_G=25Ω, Starting T_J=25°C
 2, Repetitive Rating : Pulse width limited by maximum junction temperature
 3, Pulse Test : Pulse Width ≤ 300μs, Duty Cycle ≤ 2%
 4, Essentially Independent of Operating Temperature

Typical Characteristics

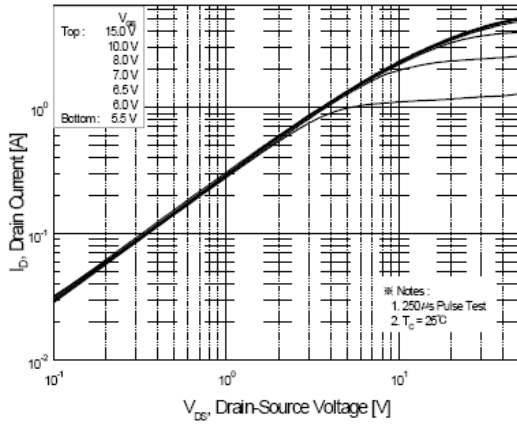


Figure 1. On-Region Characteristics

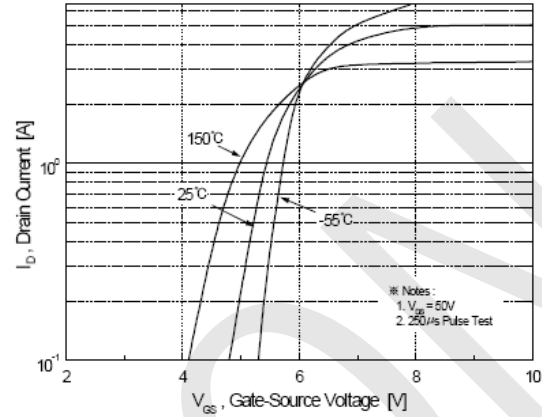


Figure 2. Transfer Characteristics

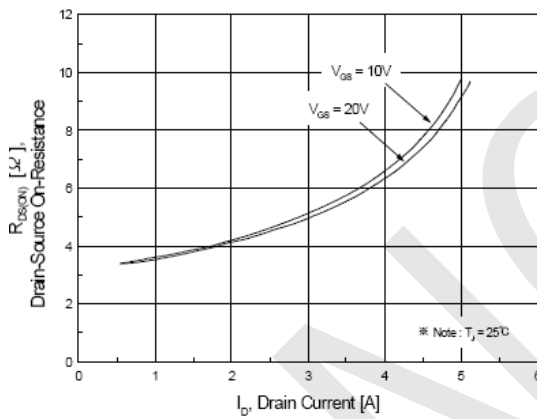


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

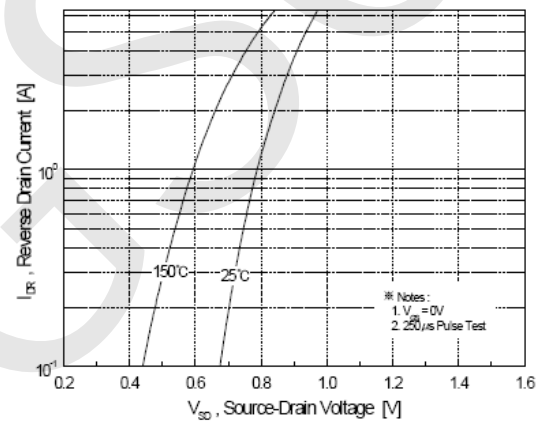


Figure 4. Body Diode Forward Voltage Variation vs. Source-Drain Voltage and Temperature

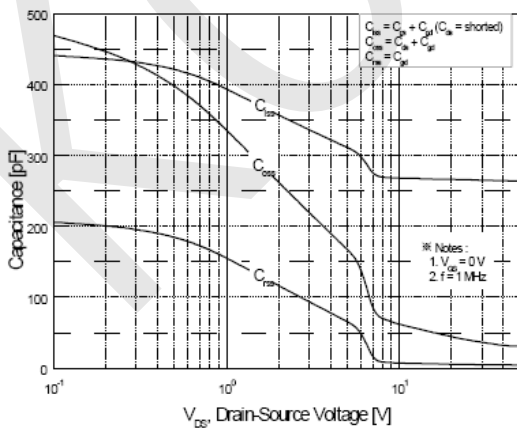


Figure 5. Capacitance Characteristics

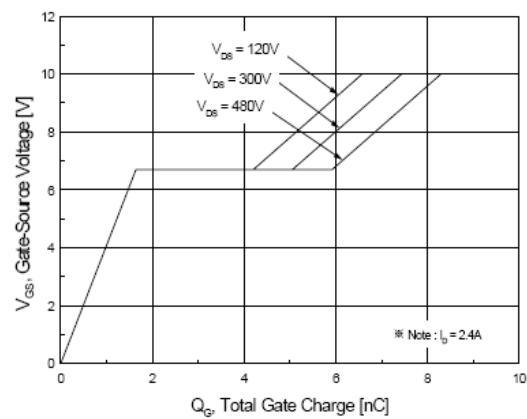


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

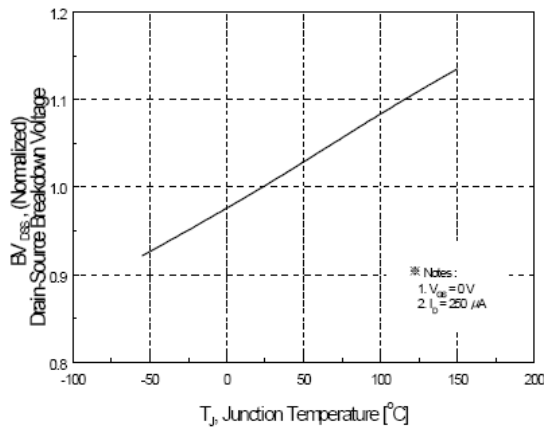


Figure 7. Breakdown Voltage Variation vs. Temperature

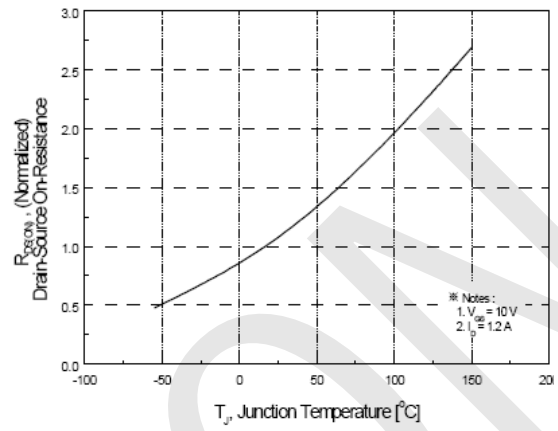


Figure 8. On-Resistance Variation vs. Temperature

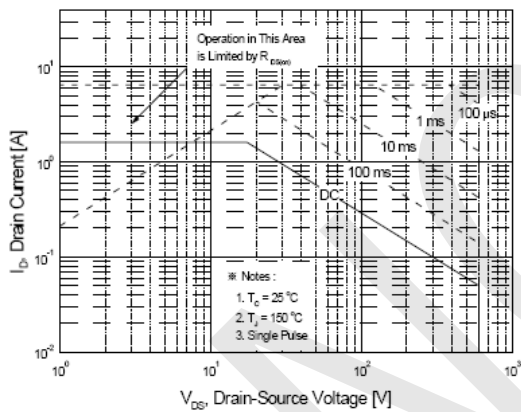


Figure 9. Maximum Safe Operating Area

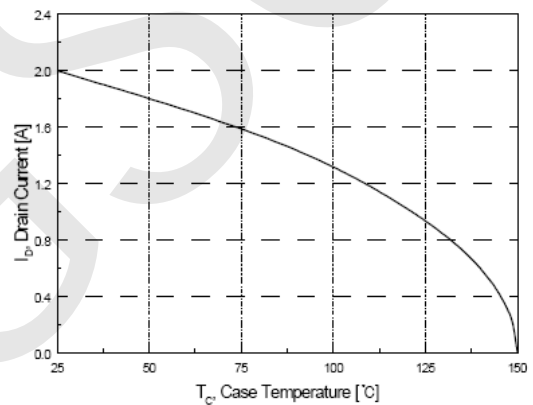


Figure 10. Maximum Drain Current vs. Case Temperature

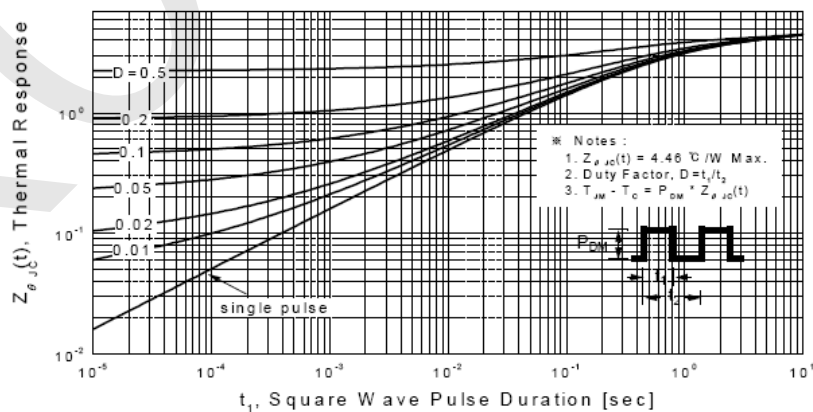
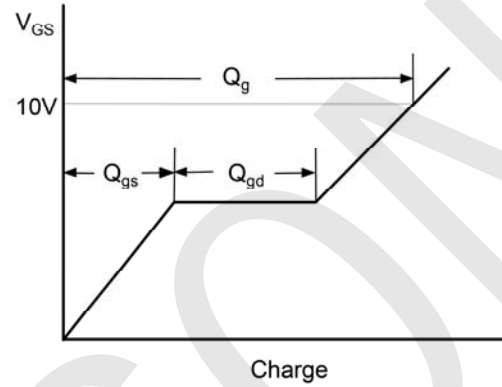
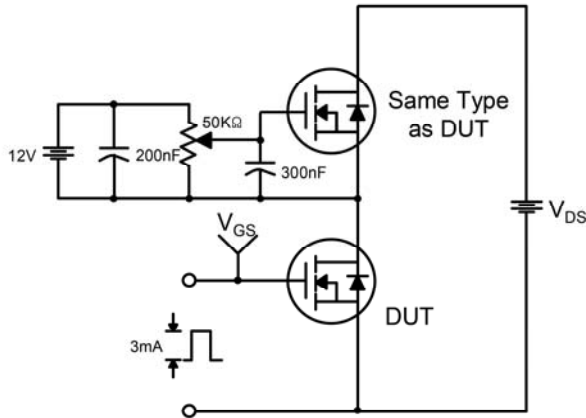
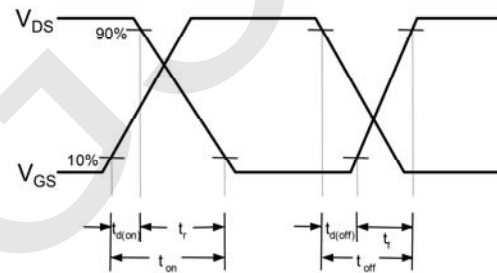
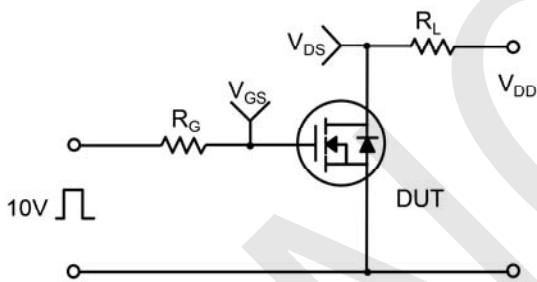


Figure 11. Transient Thermal Response Curve

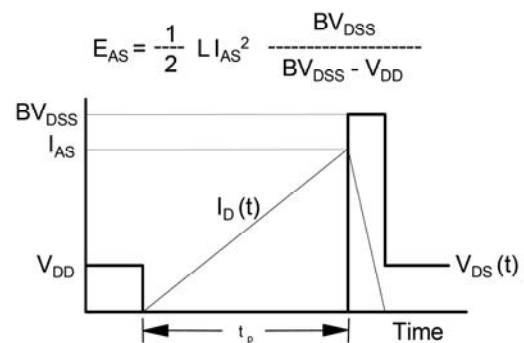
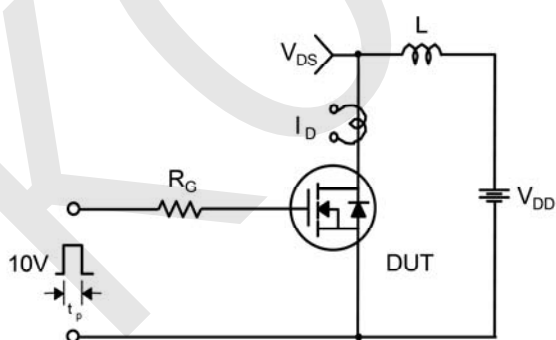
Gate Charge Test Circuit & Waveform



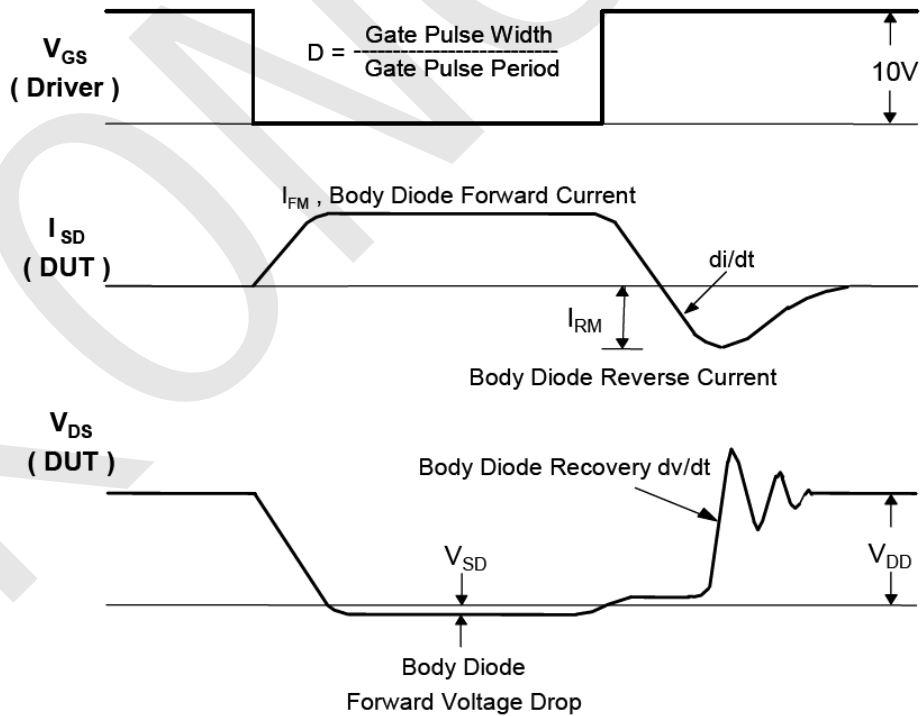
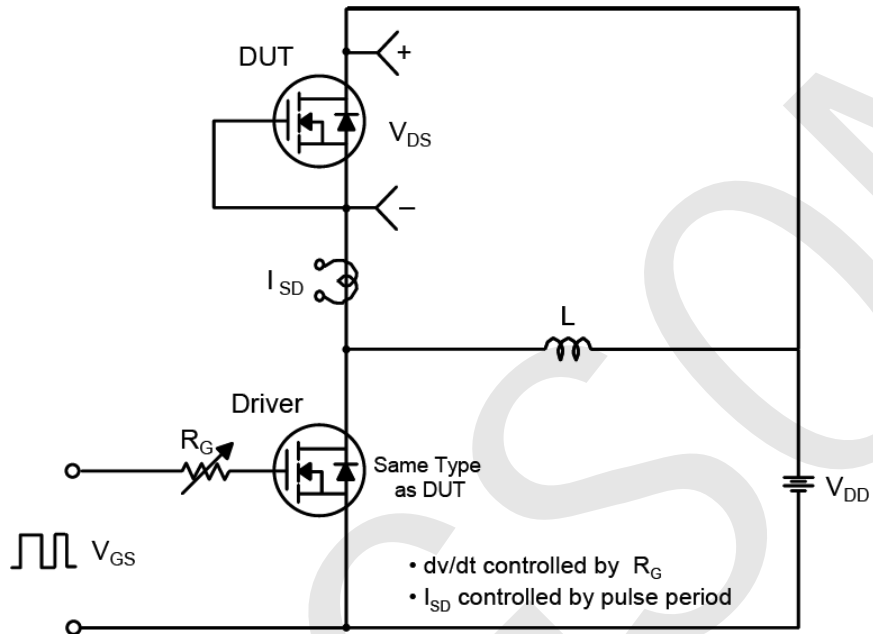
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms



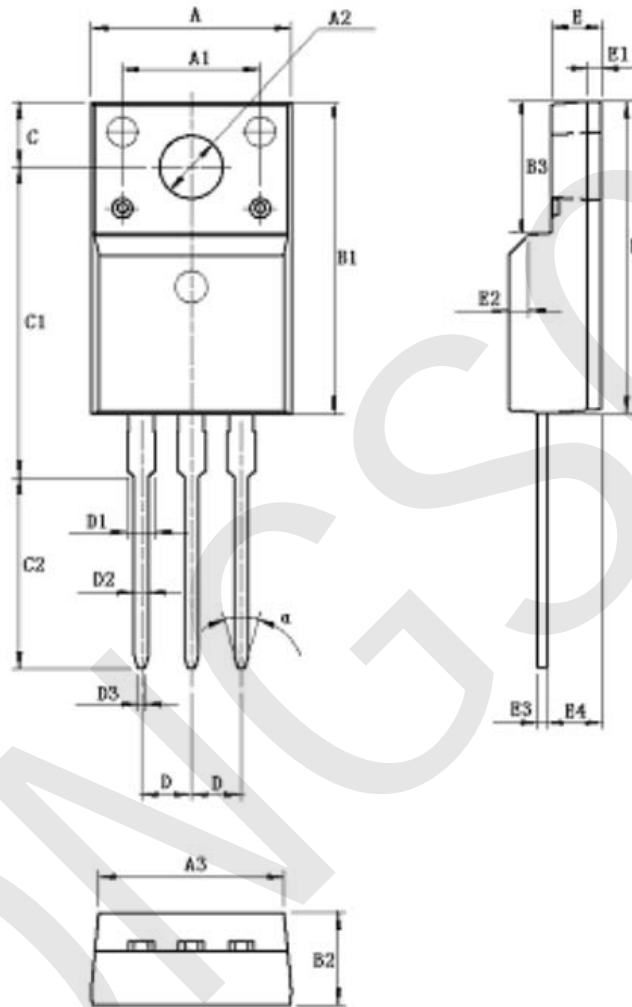
Peak Diode Recovery dv/dt Test Circuit & Waveform



Package Dimension

TO-220F

Unit: mm



| Symbol | Min | Max | Symbol | Min | Max |
|--------|-------|-------|----------|---------|------|
| A | 9.96 | 10.36 | D | 2.54 | |
| A1 | 7.00 | | D1 | 1.15 | 1.35 |
| A2 | 3.08 | 3.28 | D2 | 0.70 | 0.90 |
| A3 | 9.25 | 9.65 | D3 | 0.28 | 0.48 |
| B1 | 15.70 | 16.10 | E | 2.34 | 2.74 |
| B2 | 4.50 | 4.90 | E1 | 0.70 | |
| B3 | 6.20 | 6.80 | E2 | 1.0×45° | |
| C | 3.20 | 3.40 | E3 | 0.36 | 0.65 |
| C1 | 15.20 | 16.00 | E4 | 2.55 | 2.95 |
| C2 | 9.75 | 10.15 | a(angle) | 30° | |